

# NSBC123TDP6

## Dual NPN Bias Resistor Transistors

**R1 = 2.2 kΩ, R2 = ∞ kΩ**

### NPN Transistors with Monolithic Bias Resistor Network

This series of digital transistors is designed to replace a single device and its external resistor bias network. The Bias Resistor Transistor (BRT) contains a single transistor with a monolithic bias network consisting of two resistors; a series base resistor and a base-emitter resistor. The BRT eliminates these individual components by integrating them into a single device. The use of a BRT can reduce both system cost and board space.

#### Features

- S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- Simplifies Circuit Design
- Reduces Board Space
- Reduces Component Count
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

#### MAXIMUM RATINGS

(T<sub>A</sub> = 25°C, common for Q1 and Q2, unless otherwise noted)

Rating	Symbol	Max	Unit
Collector-Base Voltage	V <sub>CBO</sub>	50	Vdc
Collector-Emitter Voltage	V <sub>CEO</sub>	50	Vdc
Collector Current – Continuous	I <sub>C</sub>	100	mA
Input Forward Voltage	V <sub>IN(fwd)</sub>	12	Vdc
Input Reverse Voltage	V <sub>IN(rev)</sub>	6	Vdc

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

#### ORDERING INFORMATION

Device	Package	Shipping†
NSBC123TDP6T5G	SOT-963	8,000 / Tape & Reel

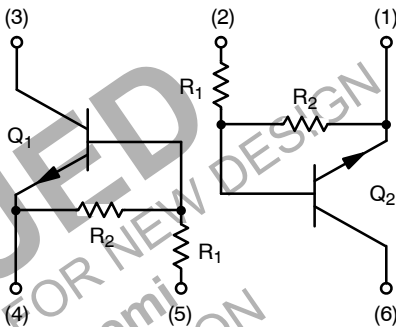
†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.



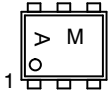
ON Semiconductor®

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#### PIN CONNECTIONS



#### MARKING DIAGRAMS



SOT-963  
CASE 527AD

A = Specific Device Code  
M = Date Code\*

\*Date Code orientation may vary depending upon manufacturing location.

# NSBC123TDP6

## THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
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### NSBC123TDP6 (SOT-963) One Junction Heated

Total Device Dissipation $T_A = 25^\circ\text{C}$ (Note 1) (Note 2) Derate above $25^\circ\text{C}$ (Note 1) (Note 2)	$P_D$	231 269 1.9 2.2	mW  mW/ $^\circ\text{C}$
Thermal Resistance, Junction to Ambient (Note 1) (Note 2)	$R_{\theta JA}$	540 464	$^\circ\text{C/W}$

### NSBC123TDP6 (SOT-963) Both Junction Heated (Note 3)

Total Device Dissipation $T_A = 25^\circ\text{C}$ (Note 1) (Note 2) Derate above $25^\circ\text{C}$ (Note 1) (Note 2)	$P_D$	339 408 2.7 3.3	mW  mW/ $^\circ\text{C}$
Thermal Resistance, Junction to Ambient (Note 1) (Note 2)	$R_{\theta JA}$	369 306	$^\circ\text{C/W}$
Junction and Storage Temperature Range	$T_J, T_{stg}$	-55 to +150	$^\circ\text{C}$

1. FR-4 @ 100 mm<sup>2</sup>, 1 oz. copper traces, still air.
2. FR-4 @ 500 mm<sup>2</sup>, 1 oz. copper traces, still air.
3. Both junction heated values assume total power is sum of two equally powered channels.

**DISCONTINUED**  
THIS DEVICE IS NOT RECOMMENDED FOR NEW DESIGN  
PLEASE CONTACT YOUR onsemi  
REPRESENTATIVE FOR INFORMATION

# NSBC123TDP6

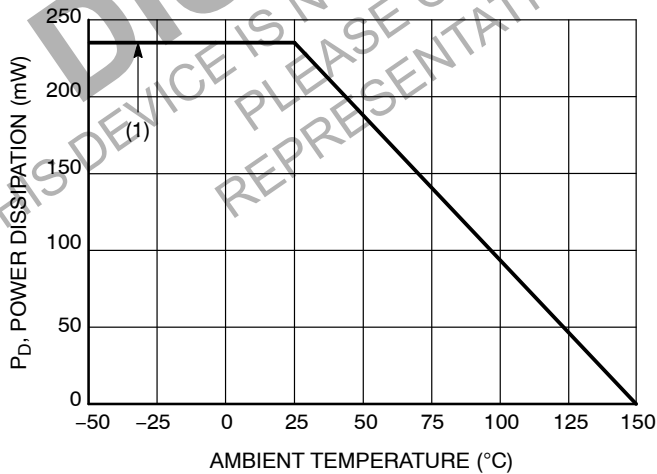
## ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ , common for $Q_1$ and $Q_2$ , unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
<b>OFF CHARACTERISTICS</b>					
Collector-Base Cutoff Current ( $V_{CB} = 50\text{ V}$ , $I_E = 0$ )	$I_{CBO}$	–	–	100	nAdc
Collector-Emitter Cutoff Current ( $V_{CE} = 50\text{ V}$ , $I_B = 0$ )	$I_{CEO}$	–	–	500	nAdc
Emitter-Base Cutoff Current ( $V_{EB} = 6.0\text{ V}$ , $I_C = 0$ )	$I_{EBO}$	–	–	4.0	mAdc
Collector-Base Breakdown Voltage ( $I_C = 10\text{ }\mu\text{A}$ , $I_E = 0$ )	$V_{(BR)CBO}$	50	–	–	Vdc
Collector-Emitter Breakdown Voltage (Note 4) ( $I_C = 2.0\text{ mA}$ , $I_B = 0$ )	$V_{(BR)CEO}$	50	–	–	Vdc

## ON CHARACTERISTICS

DC Current Gain (Note 4) ( $I_C = 5.0\text{ mA}$ , $V_{CE} = 10\text{ V}$ )	$h_{FE}$	160	350	–	
Collector-Emitter Saturation Voltage (Note 4) ( $I_C = 10\text{ mA}$ , $I_B = 1.0\text{ mA}$ )	$V_{CE(sat)}$	–	–	0.25	Vdc
Input Voltage (off) ( $V_{CE} = 5.0\text{ V}$ , $I_C = 100\text{ }\mu\text{A}$ )	$V_{i(off)}$	–	0.6	–	Vdc
Input Voltage (on) ( $V_{CE} = 0.2\text{ V}$ , $I_C = 10\text{ mA}$ )	$V_{i(on)}$	–	0.9	–	Vdc
Output Voltage (on) ( $V_{CC} = 5.0\text{ V}$ , $V_B = 2.5\text{ V}$ , $R_L = 1.0\text{ k}\Omega$ )	$V_{OL}$	–	–	0.2	Vdc
Output Voltage (off) ( $V_{CC} = 5.0\text{ V}$ , $V_B = 0.25\text{ V}$ , $R_L = 1.0\text{ k}\Omega$ )	$V_{OH}$	4.9	–	–	Vdc
Input Resistor	$R_1$	1.5	2.2	2.9	$\text{k}\Omega$
Resistor Ratio	$R_1/R_2$	–	–	–	

4. Pulsed Condition: Pulse Width = 300 msec, Duty Cycle  $\leq$  2%.



(1) SOT-963; 100 mm<sup>2</sup>, 1 oz. copper trace

Figure 1. Derating Curve

TYPICAL CHARACTERISTICS  
NSBC123TDP6

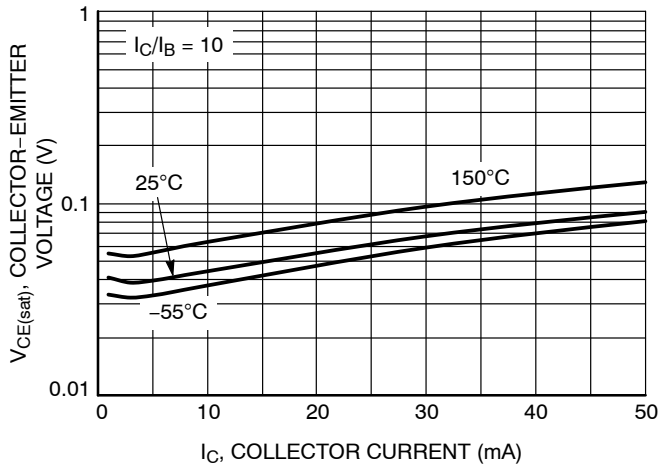


Figure 2.  $V_{CE(sat)}$  vs.  $I_C$

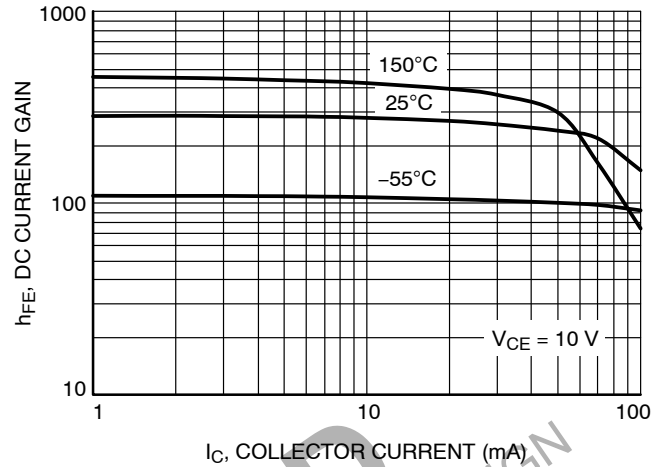


Figure 3. DC Current Gain

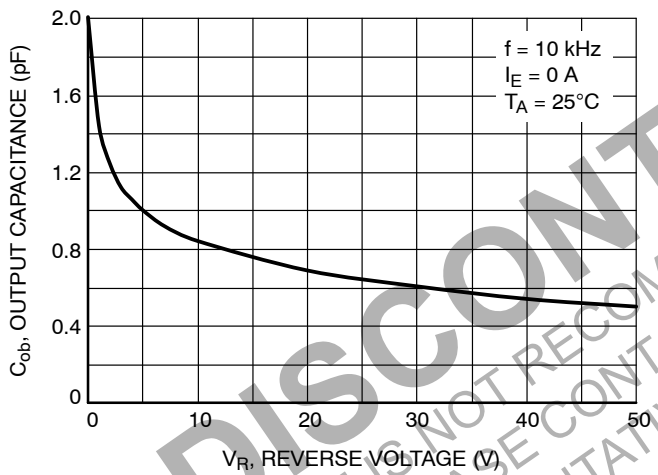


Figure 4. Output Capacitance

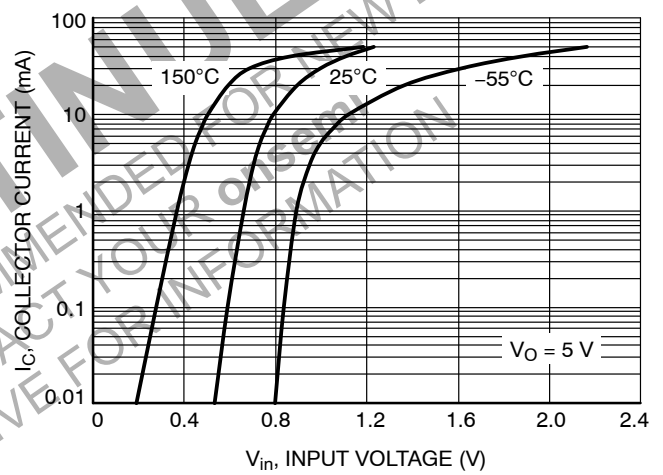


Figure 5. Output Current vs. Input Voltage

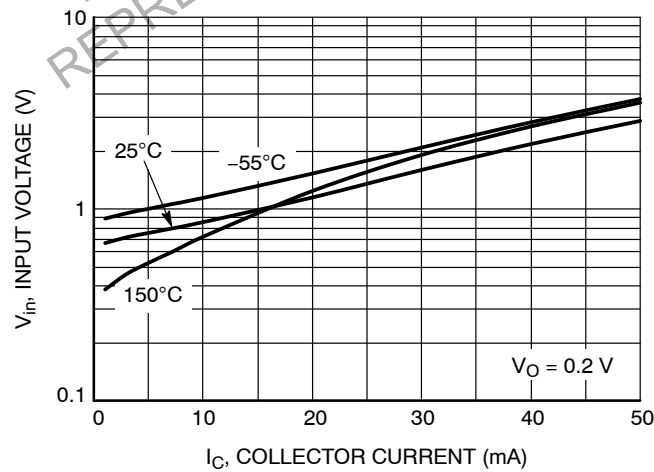
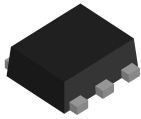


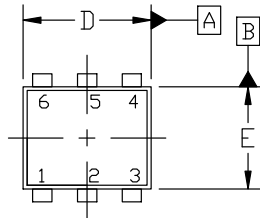
Figure 6. Input Voltage vs. Output Current


**SOT-963 1.00x1.00x0.37, 0.35P**  
**CASE 527AD**  
**ISSUE F**

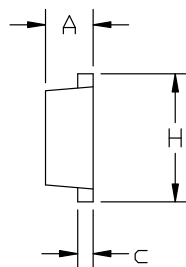
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## NOTES:

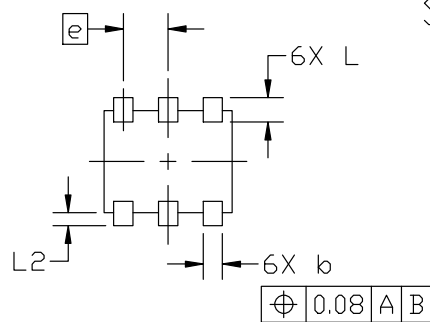
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.



TOP VIEW

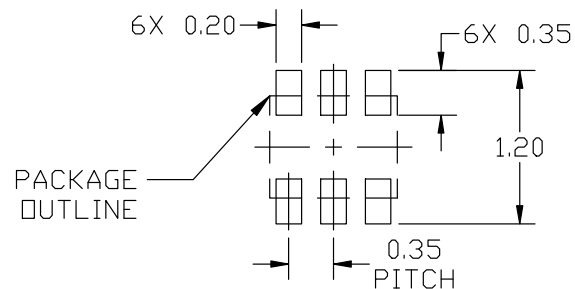


SIDE VIEW



BOTTOM VIEW

DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.34	0.37	0.40
b	0.10	0.15	0.20
c	0.07	0.12	0.17
D	0.95	1.00	1.05
E	0.75	0.80	0.85
e	0.35 BSC		
H	0.95	1.00	1.05
L	0.19 REF		
L2	0.05	0.10	0.15


RECOMMENDED MOUNTING  
FOOTPRINT

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference manual, SOLDERRM/D.

## STYLE 1:

- PIN 1. EMITTER 1
2. BASE 1
3. COLLECTOR 2
4. EMITTER 2
5. BASE 2
6. COLLECTOR 1

## STYLE 2:

- PIN 1. EMITTER 1
2. EMITTER 2
3. BASE 2
4. COLLECTOR 2
5. BASE 1
6. COLLECTOR 1

## STYLE 3:

- PIN 1. CATHODE 1
2. CATHODE 1
3. ANODE/ANODE 2
4. CATHODE 2
5. CATHODE 2
6. ANODE/ANODE 1

## STYLE 4:

- PIN 1. COLLECTOR
2. COLLECTOR
3. BASE
4. EMITTER
5. COLLECTOR
6. COLLECTOR

## STYLE 5:

- PIN 1. CATHODE
2. CATHODE
3. ANODE
4. ANODE
5. CATHODE
6. CATHODE

## STYLE 6:

- PIN 1. CATHODE
2. ANODE
3. CATHODE
4. CATHODE
5. CATHODE
6. CATHODE

## STYLE 7:

- PIN 1. CATHODE
2. ANODE
3. CATHODE
4. CATHODE
5. ANODE
6. CATHODE

## STYLE 8:

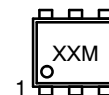
- PIN 1. DRAIN
2. DRAIN
3. GATE
4. SOURCE
5. DRAIN
6. DRAIN

## STYLE 9:

- PIN 1. SOURCE 1
2. GATE 1
3. DRAIN 2
4. SOURCE 2
5. GATE 2
6. DRAIN 1

## STYLE 10:

- PIN 1. CATHODE 1
2. N/C
3. CATHODE 2
4. ANODE 2
5. N/C
6. ANODE 1

**GENERIC  
MARKING DIAGRAM\***

XX = Specific Device Code  
M = Month Code

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

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